

NOT RECOMMENDED FOR NEW DESIGN USE ZXTN4240F



DSS4240T

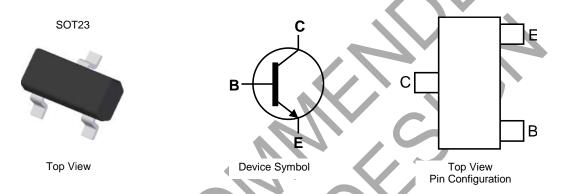
40V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

- BV_{CEO} > 40V
- I_C = 2A High Continuous Collector Current
- I_{CM} = 3A Peak Pulse Current
- Low Saturation Voltage 180mV Max @ I_C = 1A
- R_{CE(SAT)} = 60mΩ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary PNP Type: DSS5240T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 3
- Weight: 0.008 grams (Approximate)



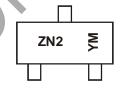
Ordering Information (Note 4)

Product	Compliance	Marking		Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS4240T-7	NRND (use ZXTN4240F-7)	ZN2	_	7	8	3000
DSS4240T-13	NRND (use ZXTN4240F-7)	ZN2		13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.
- 5. NRND Not recommended for new design.

Marking Information



ZN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Kev

Year	2013	2014	2015	2016	2017	2018	3 20	19	2020	2021	2022	2023
Code	Α	В	С	D	Е	F	G	;	Н	ı	J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	А
Continuous Collector Current	Ic	2	A
Peak Base Current	I _{BM}	0.3	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	730	mW
Power Dissipation (Note 7)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\Theta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 7)	R _{OJA}	209	°C/W
Thermal Resistance, Junction to Lead (Note 8)	R _Ð JL	75	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

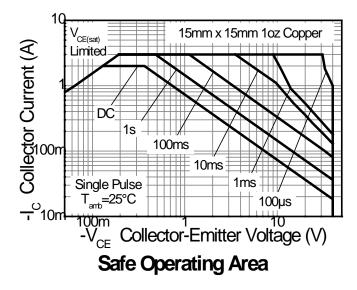
 7. Same as Note 5, except the device is mounted on minimum recommended pad layout.

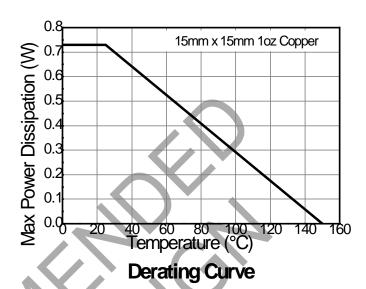
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

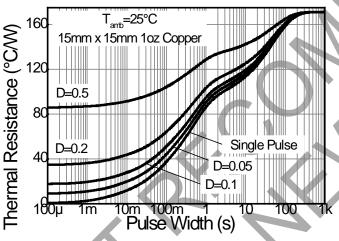
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

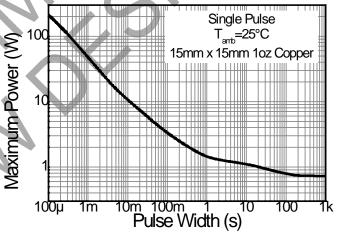


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation

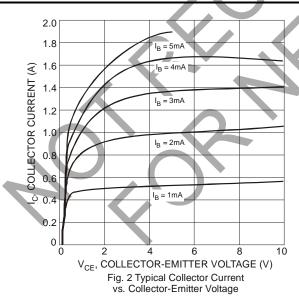


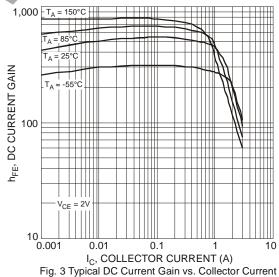
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	40	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	40			V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	1	1	V	$I_E = 100\mu A$
Collector-Base Cutoff Current	lana	1	1	100	nA	$V_{CB} = 30V, I_E = 0$
Collector-base Cutoff Current	I _{CBO}	I	I	50	μΑ	$V_{CB} = 30V, I_E = 0, T_A = +150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}	l	1	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 8)					•	
		350	1	-		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h	300	I			$V_{CE} = 2V, I_{C} = 0.5A$
De current Gain	h _{FE}	300	1	1		$V_{CE} = 2V$, $I_C = 1A$
		150	1			$V_{CE} = 2V$, $I_C = 2A$
		I	I	70	,	$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
		-	30	100		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	1	180	mV	$I_C = 750 \text{mA}, I_B = 15 \text{mA}$
		I		180		$I_C = 1A$, $I_B = 50mA$
				320		$I_C = 2A$, $I_B = 200mA$
Equivalent On-Resistance	R _{CE(sat)}	_	60	200	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	+		1.1	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-on Voltage	V _{BE(on)}		1	0.75	V	V _{CE} = 2V, I _C = 100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	-		MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Output Capacitance	Cob		_	20	рF	V _{CB} = 10V, f = 1MHz

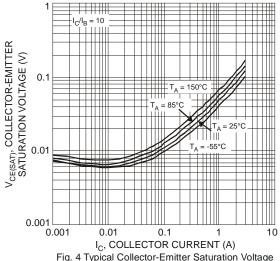
Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

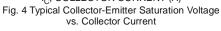
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

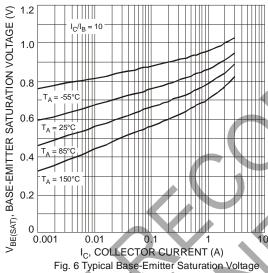












vs. Collector Current

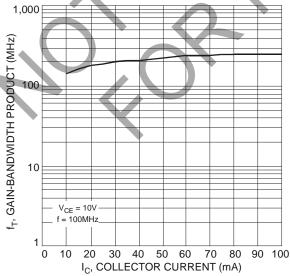
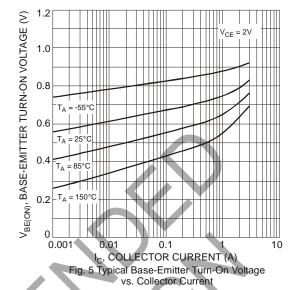
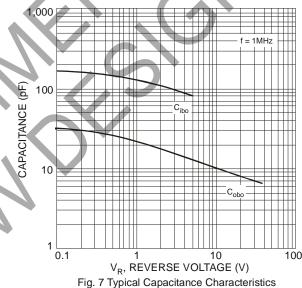


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current





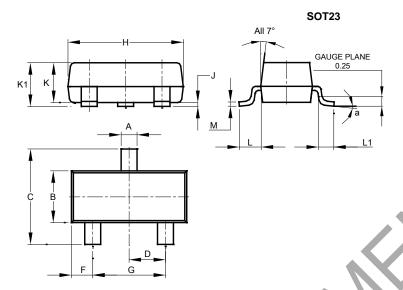
DSS4240T

Document number: DS31623 Rev. 6 - 3



Package Outline Dimensions

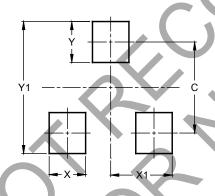
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°	_				
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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